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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO	
10/021,497	12/19/2001	William G. En	50432-477	1401	
7:	590 05/08/2003				
McDERMOTT, WILL & EMERY			EXAMINER		
600 13th Street, N.W. Washington, DC 20005-3096			SOWARD, IDA M		
			ART UNIT	PAPER NUMBER	
			2822	·	
			DATE MAILED: 05/08/2003		

Please find below and/or attached an Office communication concerning this application or proceeding.

		A	pplication No.	Applicant(s)	
Y			0/021,497	EN ET AL.	
Office Action Summa		Examiner		Art Unit	
-		Id	a M Soward	2822	
Period fo	The MAILING DATE of this comm or Reply	unication appear	s on the cover sheet w	th the correspondence address	
THE I - Exter after - If the - If NO - Failu - Any r	ORTENED STATUTORY PERIOD MAILING DATE OF THIS COMMUNICATION OF THIS COMMUNICATION OF THIS COMMUNICATION OF THE PROPERTY OF THIS COMMUNICATION OF THE PROPERTY	JNICATION. ions of 37 CFR 1.136(a) ommunication. by (30) days, a reply with n statutory period will ap eply will, by statute, cau hs after the mailing date	in no event, however, may a main the statutory minimum of thir oply and will expire SIX (6) MON se the application to become Al	eply be timely filed y (30) days will be considered timely. THS from the mailing date of this communications SANDONED (35 U.S.C. § 133).	cation.
1)🖂	Responsive to communication(s)) filed on <u>20 Feb</u>	ruary 2003 .		
2a)	This action is FINAL .	_	ction is non-final.		
3)□ Dispositi	Since this application is in condit closed in accordance with the proof on of Claims				rits is
4)⊠	Claim(s) <u>1-6,8 and 10-22</u> is/are p	ending in the ap	plication.		
	4a) Of the above claim(s) <u>11-20</u> is	/are withdrawn f	rom consideration.		
_	Claim(s) is/are allowed.				
	Claim(s) <u>1-6,8,10,21 and 22</u> is/are	e reiected.			
	Claim(s) is/are objected to.	-			
	Claim(s) are subject to rest		ection requirement		
	on Papers		ouen requirement.		
9) 🔲 -	The specification is objected to by	the Examiner.			
10) 🔲 🗆	The drawing(s) filed on is/ar	re: a) accepted	or b) objected to by t	ne Examiner.	
	Applicant may not request that any		•		
11) 🖂 🗆	The proposed drawing correction fi	iled on <u>20 Febru</u>	<i>ary 2003</i> is: a)⊠ appro	oved b) disapproved by the E	Examine
	If approved, corrected drawings are	required in reply to	this Office action.		
12) 🔲 🗆	The oath or declaration is objected	to by the Exami	ner.		
Priority u	nder 35 U.S.C. §§ 119 and 120				
13)	Acknowledgment is made of a cla	im for foreign pri	ority under 35 U.S.C.	§ 119(a)-(d) or (f).	
_	☐ All b)☐ Some * c)☐ None of	•	•		
	1. Certified copies of the priori		ve been received.		
	2. Certified copies of the priori	•		oplication No.	
	<u> </u>	es of the priority of ernational Bureau	documents have been u (PCT Rule 17.2(a)).	received in this National Stage	;
14) 🗌 A	cknowledgment is made of a clain	n for domestic pr	iority under 35 U.S.C.	§ 119(e) (to a provisional appli	cation).
_ `	☐ The translation of the foreign lacknowledgment is made of a clair	• • •	• •		
Attachment	_	·	-		
2) D Notice	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review nation Disclosure Statement(s) (PTO-1449)	•	5) Notice of I	Summary (PTO-413) Paper No(s) nformal Patent Application (PTO-152)	"
6. Patent and Tra FO-326 (Rev		Office Action	Summary	Part of Paper No. 11	

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DETAILED ACTION

This Office Action is in response to the Applicants' amendment filed February 20, 2003.

Drawings

The objection to the drawings as failing to comply with 37 CFR 1.84(p)(4) has been withdrawn due to the amendment filed.

The objection to the drawings as failing to comply with 37 CFR 1.84(p)(5) has been withdrawn due to the amendment filed.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1-6, 8, 10 and 21-22 are rejected under 35 U.S.C. 103(a) as being unpatentable over Admitted Prior Art Figure 7 in view of Tuan et al. (US 2002/0151141 A1) and Baliga (US 2002/0177277 A1).

Admitted Prior Art Figure 7 teaches a wafer comprising: a base layer 42; an active region in the base; a gate dielectric layer 46 formed on the active region; a

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conductive layer 50 formed on the gate dielectric layer; a plurality of shallow trench isolation regions 44 formed in the wafer; and a metal interconnect layer 54 formed over the conductive layer. However, Admitted Prior Art Figure 7 fails to teach a wafer being divided into a plurality of first, second and third portions. Tuan et al. teach a wafer being divided into a plurality of first, second and third portions; the first portion comprise gate dielectric capacitor (a transistor), the gate dielectric capacitors comprise a first electrode layer 124, an insulating layer 108, and a second electrode layer 128 made of polysilicon contacting an isolation region 1010; wherein the first electrode layer is formed from the active layer, the insulating layer is formed from the gate dielectric layer, and the second electrode is formed from the conductive layer; and the third portions (containing no active layer) comprise second dummy structures 141, the second dummy structures comprise an insulating layer and a second electrode layer; wherein the insulating layer of the second dummy structures is formed from an isolation region 1010 and the second electrode layer of the second dummy structures if formed from the conductive layer (Figure 3, page 3, paragraphs [0034]-[0042]). Baliga teaches the second portions comprise first dummy structures 118c, the first dummy structures comprise a first electrode layer and an insulating layer; wherein the first electrode layer of the first dummy structures is formed from the doped silicon active layer 32 and the insulating layer of the first dummy structures is formed from the gate dielectric layer and not containing a conductive layer (Figure 11, page 8, paragraph [0056]). Since Admitted Prior Art Figure 7, Tuan et al. and Baliga are from the same field of endeavor (semiconductor devices), the purposed disclosed by Baliga would have been

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recognized in the pertinent art of Admitted Prior Art Figure 7 and Tuan et al. Therefore, it would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the gate dielectric structure of Admitted Prior Art Figure 7 with the first, second and third portions of Tuan et al. and the dummy structures of Baliga to provide a structure that can support high voltages (page 2, paragraph [0013]).

Response to Arguments

Applicant's arguments with respect to claims 1-6, 8, 10 and 21-22 have been considered but are moot in view of the new ground(s) of rejection.

Conclusion

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

The following patents are cited to further show the state of the art with respects to dummy structure devices:

Chatterjee et al. (6,015,992) Kitano (5,585,289)

Kuroi et al. (5,889,335) Narita (5,410,161).

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Ida M Soward whose telephone number is 703-305-3308. The examiner can normally be reached on Monday - Thursday, 6:30 am to 5:00 pm.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Amir Zarabian can be reached on 703-308-4905. The fax phone numbers for the organization where this application or proceeding is assigned are 703-872-9318

for regular communications and 703-872-9319 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0956.

ims May 3, 2003

> ANIR ZARABIAN SUPERVISORY PATENT EXACTINER TECHNOLOGY CENTER 2800

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